

50N06

Power MOSFET

50 Amps, 60 Volts
N-CHANNEL POWER MOSFET

■ DESCRIPTION

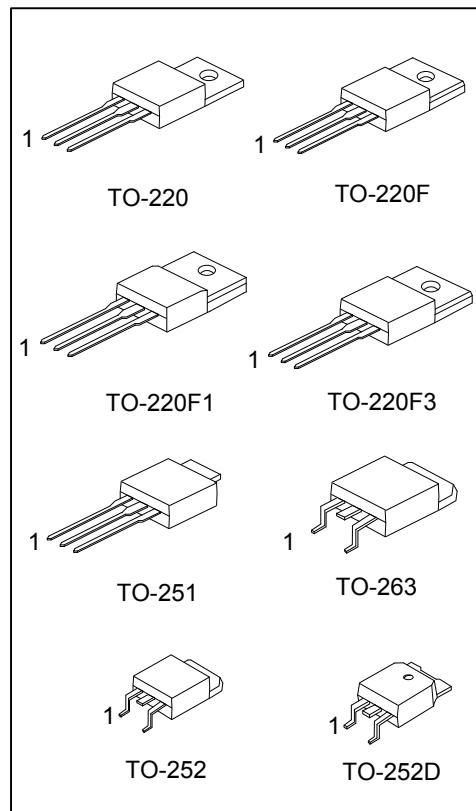
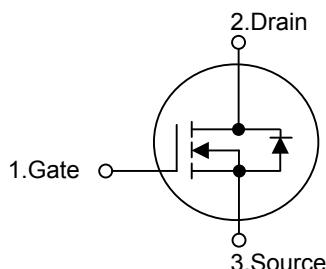
The UTC **50N06** is three-terminal silicon device with current conduction capability of about 50A, fast switching speed. Low on-state resistance, breakdown voltage rating of 60V, and max threshold voltages of 4 volt.

It is mainly suitable electronic ballast, and low power switching mode power appliances.

■ FEATURES

- * $R_{DS(ON)} < 23m\Omega$ @ $V_{GS}=10V$, $I_D=25A$
- * Fast switching capability
- * 100% avalanche energy specified
- * Improved dv/dt capability

■ SYMBOL



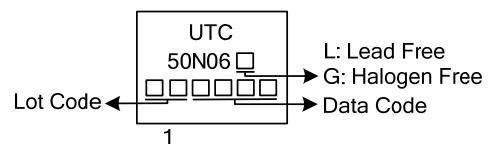
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
50N06L-TA3-T	50N06G-TA3-T	TO-220	G	D	S	Tube
50N06L-TF1-T	50N06G-TF1-T	TO-220F1	G	D	S	Tube
50N06L-TF3-T	50N06G-TF3-T	TO-220F	G	D	S	Tube
50N06L-TF3T-T	50N06G-TF3T-T	TO-220F3	G	D	S	Tube
50N06L-TM3-T	50N06G-TM3-T	TO-251	G	D	S	Tube
50N06L-TN3-R	50N06G-TN3-R	TO-252	G	D	S	Tape Reel
50N06L-TND-R	50N06G-TND-R	TO-252D	G	D	S	Tape Reel
50N06L-TQ2-T	50N06G-TQ2-T	TO-263	G	D	S	Tube
50N06L-TQ2-R	50N06G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

50N06G-TA3-T	(1) Packing Type	(1) T: Tube, R: Tape Reel
	(2) Package Type	(2) TA3: TO-220, TF1: TO-220F1, TF3: TO-220F, TF3T: TO-220F3, TM3: TO-251, TN3: TO-252, TND: TO-252DTQ2: TO-263
	(3) Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	60	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current		I _D	50	A
Pulsed Drain Current (Note 2)		I _{DM}	150	A
Avalanche Energy	Single Pulsed (Note 3)	E _{AS}	205	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	3.6	V/ns
Power Dissipation (T _C =25°C)	TO-220/TO-263	P _D	120	W
	TO-220F/TO-220F1		70	W
	TO-220F3			
	TO-251/TO-252		46	W
	TO-252D			
Junction Temperature		T _J	+150	°C
Operation and Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. L=0.1mH, I_{AS}=64A, V_{DD}= 25V, R_G=20Ω, Starting T_J=25°C

4. I_{SD}≤30A, di/dt ≤200A/μs, V_{DD}≤BV_{DSS}, Starting T_J=25°C

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/TO-220F	θ _{JA}	62	°C/W
	TO-220F1/TO-220F3			
Junction to Case	TO-263	θ _{JC}	100	°C/W
	TO-251/TO-252			
	TO-252D			
	TO-220		1.24	°C/W
	TO-220F/TO-220F1		1.78	°C/W
	TO-220F3			
	TO-251/TO-252		2.7	°C/W
	TO-252D			
	TO-263		1.24	°C/W

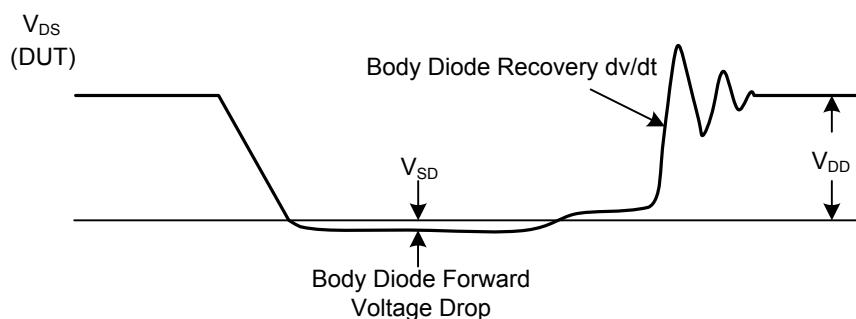
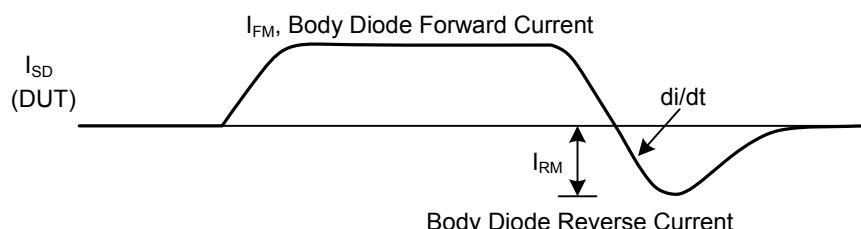
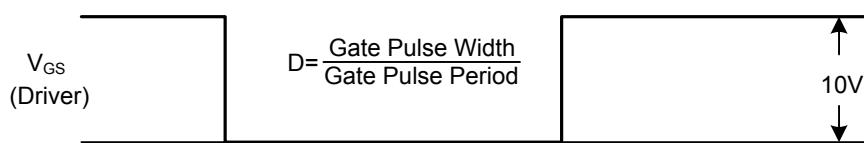
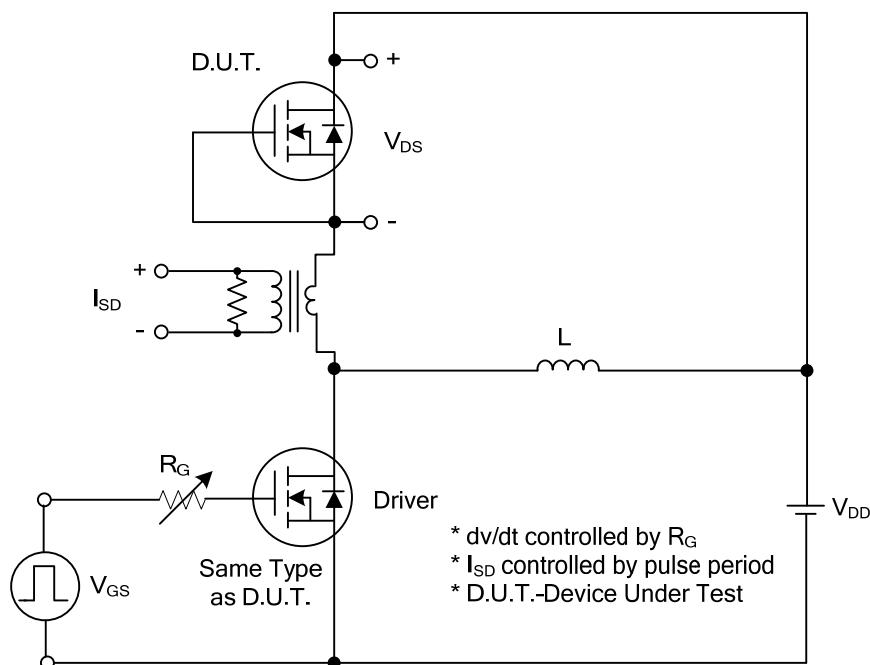
■ ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_D=250\mu\text{A}$	60			V
Drain-Source Leakage Current	I_{DSS}	$\text{V}_{\text{DS}}=60\text{V}, \text{V}_{\text{GS}}=0\text{V}$		10		μA
Gate-Source Leakage Current	Forward	$\text{V}_{\text{GS}}=20\text{V}, \text{V}_{\text{DS}}=0\text{V}$		100		nA
	Reverse	$\text{V}_{\text{GS}}=-20\text{V}, \text{V}_{\text{DS}}=0\text{V}$		-100		nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$\text{V}_{\text{GS(TH)}}$	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_D=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$\text{R}_{\text{DS(ON)}}$	$\text{V}_{\text{GS}}=10\text{V}, \text{I}_D=25\text{A}$		23		$\text{m}\Omega$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$\text{V}_{\text{GS}}=0\text{V}, \text{V}_{\text{DS}}=25\text{V}, f=1\text{MHz}$		1200		pF
Output Capacitance	C_{OSS}			580		pF
Reverse Transfer Capacitance	C_{RSS}			180		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q_G	$\text{V}_{\text{DS}}=50\text{V}, \text{V}_{\text{GS}}=10\text{V}, \text{I}_D=1.3\text{A}$ $\text{I}_G=100\mu\text{A}$ (Note1,2)		145		nC
Gate-Source Charge	Q_{GS}			10		nC
Gate-Drain Charge	Q_{GD}			36		nC
Turn-On Delay Time	$t_{\text{D(ON)}}$	$\text{V}_{\text{DD}}=30\text{V}, \text{V}_{\text{GS}}=10\text{V}, \text{I}_D=50\text{A},$ $\text{R}_G=25\Omega$ (Note1,2)		18		ns
Turn-On Rise Time	t_R			84		ns
Turn-Off Delay Time	$t_{\text{D(OFF)}}$			62		ns
Turn-Off Fall Time	t_F			48		ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				50	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				150	A
Drain-Source Diode Forward Voltage	V_{SD}	$\text{I}_S=50\text{A}, \text{V}_{\text{GS}}=0\text{V}$			1.5	V
Reverse Recovery Time	t_{rr}	$\text{I}_S=30\text{A}, \text{V}_{\text{GS}}=0\text{V}$ $d\text{I}_F/dt=100\text{A}/\mu\text{s}$		90		ns
Reverse Recovery Charge	Q_{rr}			260		nC

Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS



Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS

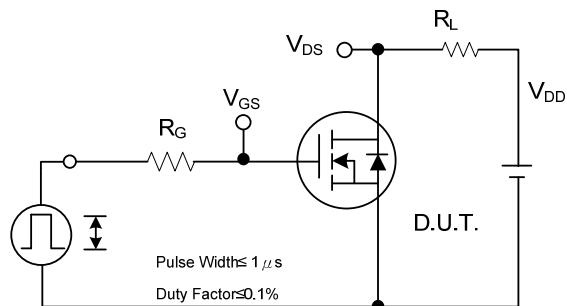


Fig. 2A Switching Test Circuit

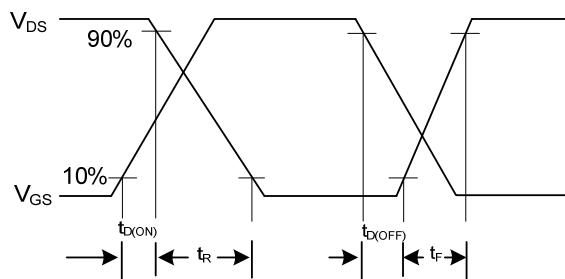


Fig. 2B Switching Waveforms

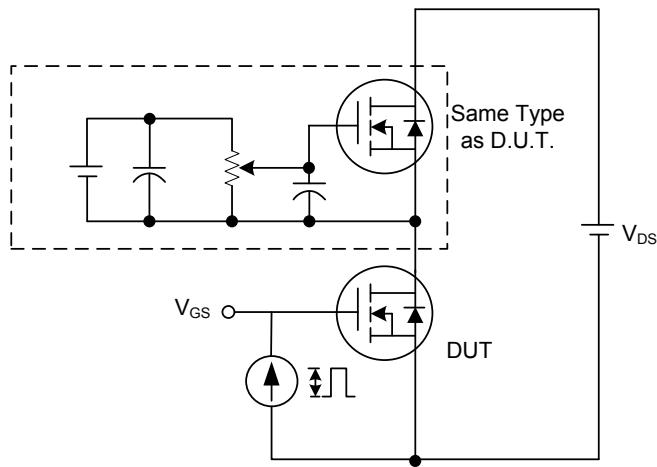


Fig. 3A Gate Charge Test Circuit

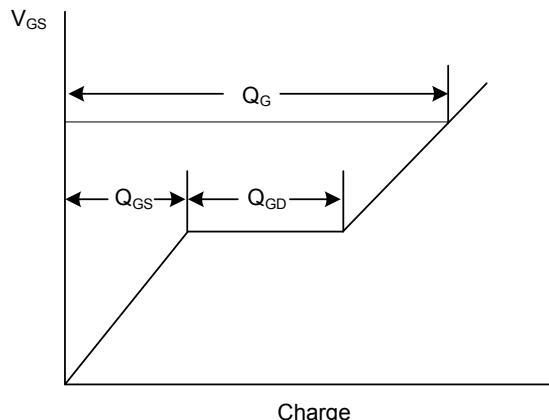


Fig. 3B Gate Charge Waveform

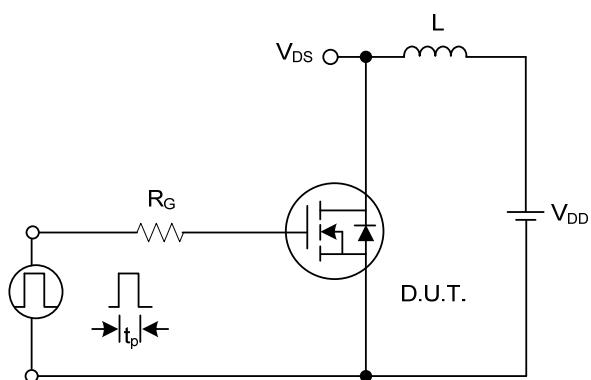


Fig. 4A Unclamped Inductive Switching Test Circuit

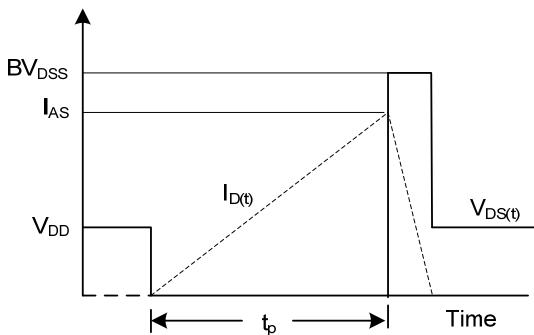
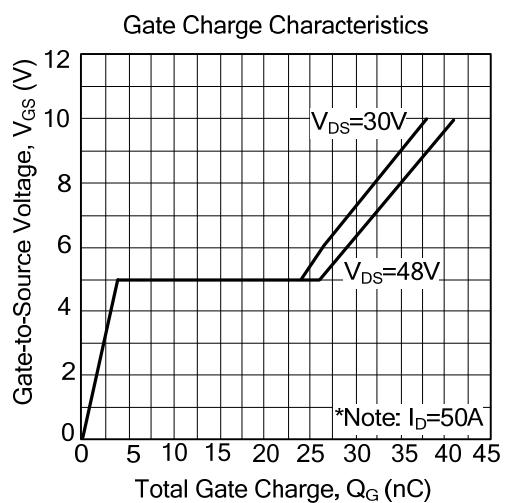
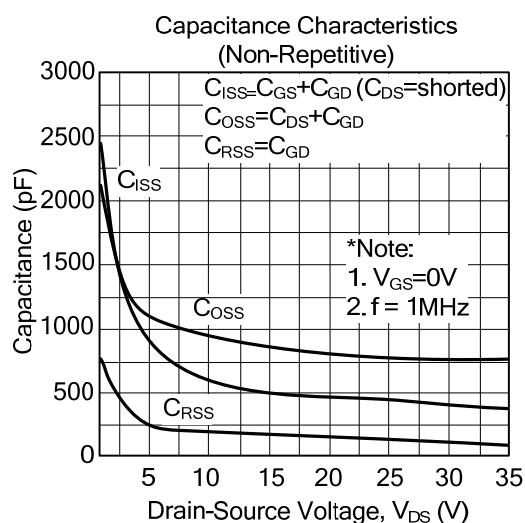
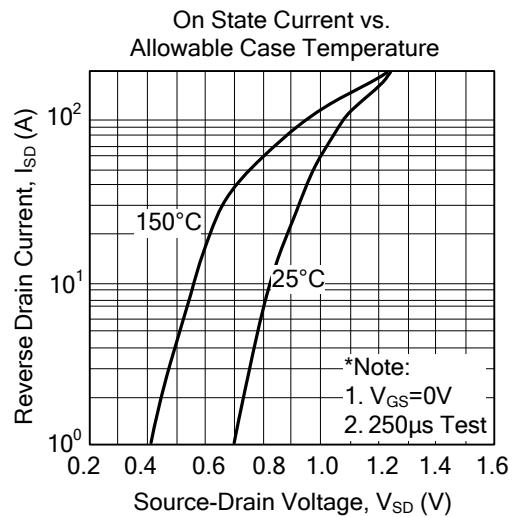
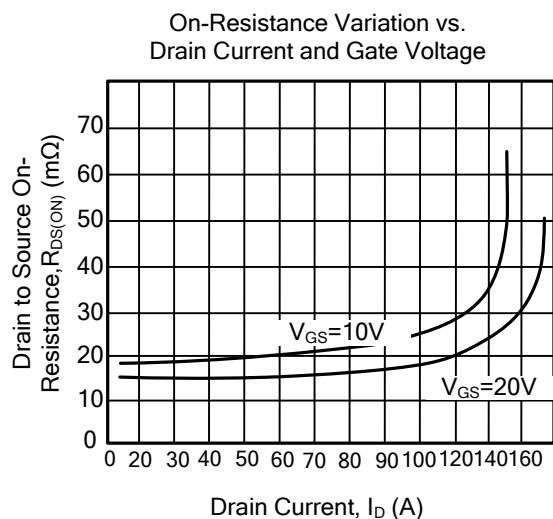
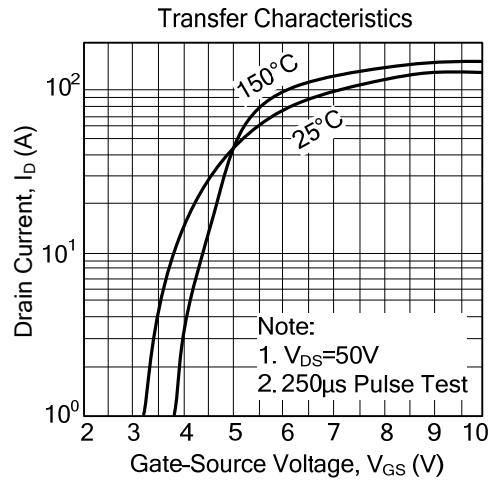
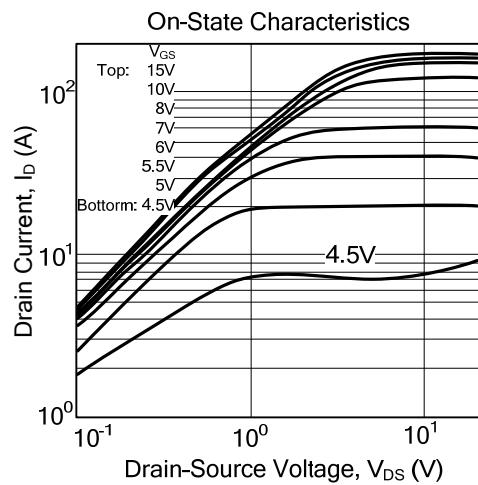
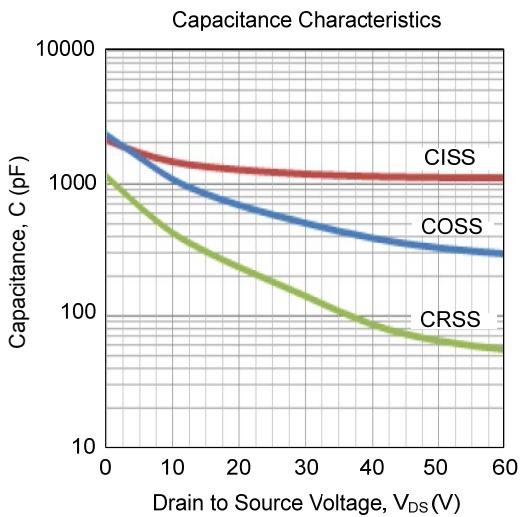
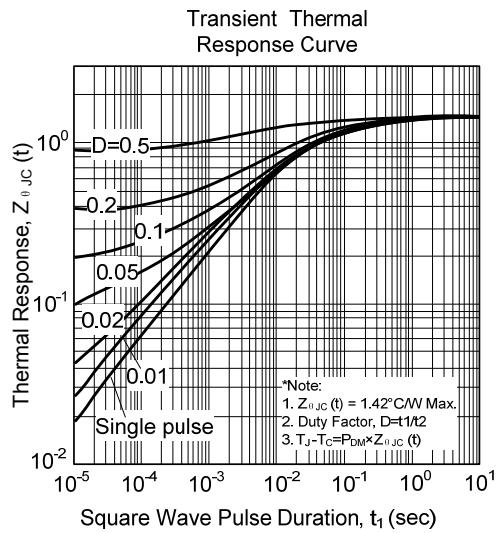
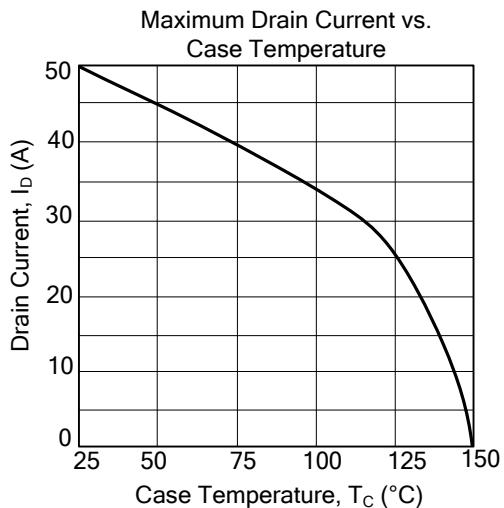
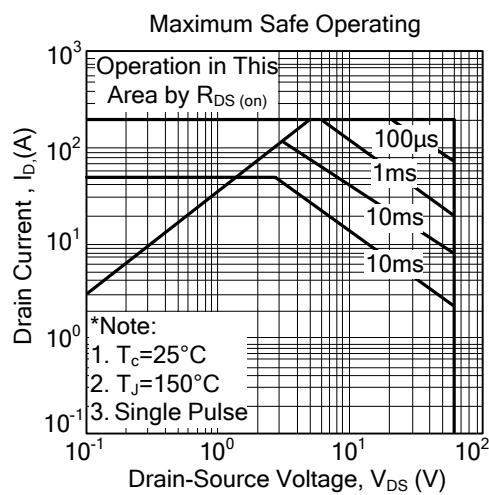
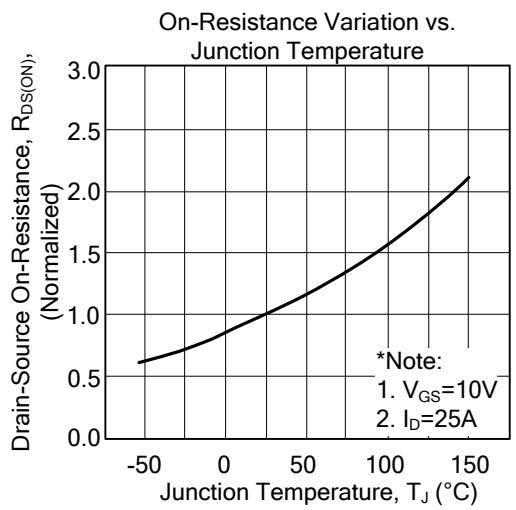
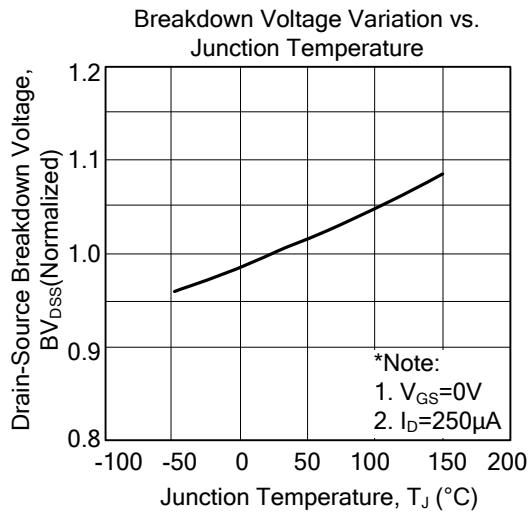


Fig. 4B Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS(Cont.)



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